

Electron Beam Lithography on Irregular Surfaces Using an Evaporated Resist

Jian Zhang, Celal Con, and Bo Cui*

Department of Electrical and Computer Engineering and Waterloo Institute for Nanotechnology (WIN), University of Waterloo, Waterloo, Ontario N2L 3G1, Canada

Gergő Fülöp

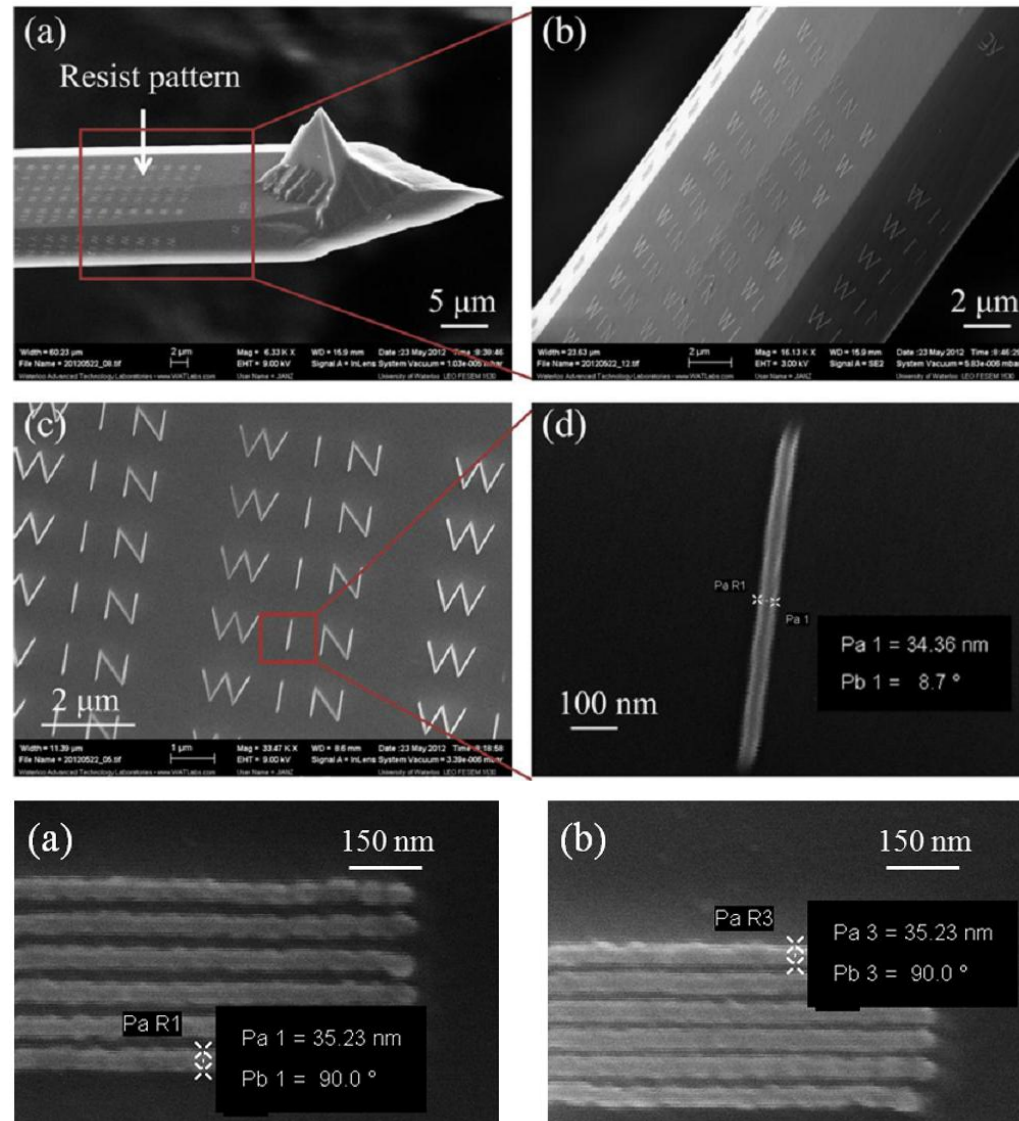
NanoJC

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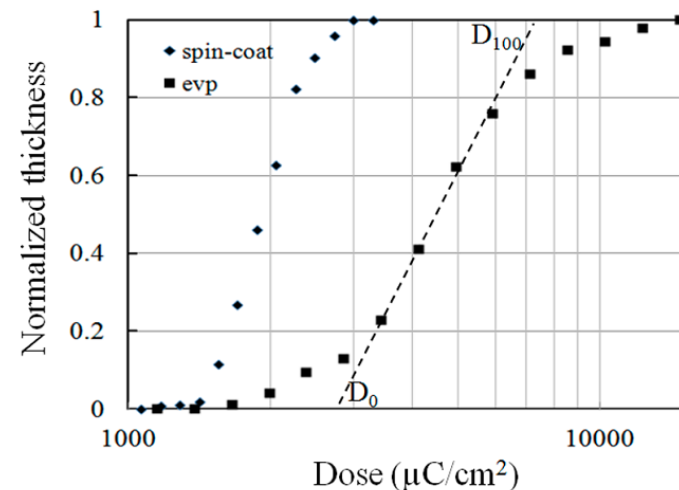
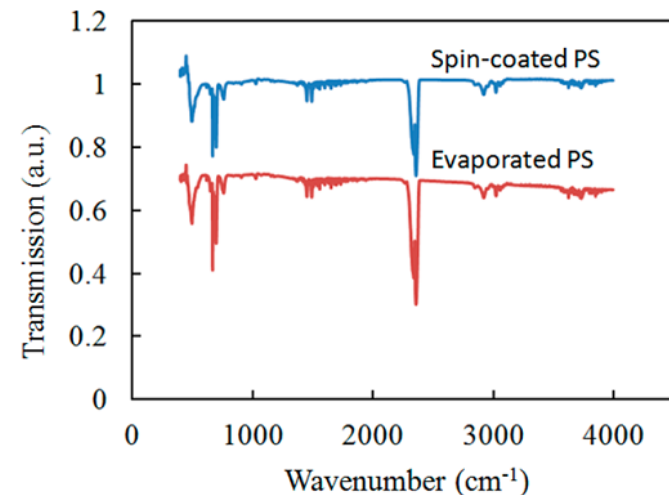
EBL with Evaporated Resist

- Non-planar, irregular, fragile substrate
- optical fiber: lab-on-fiber technology
 - coupling to a metallic nanostructure
- resist deposition methods
 - spinning (low viscosity)
 - spray coating
 - Langmuir-Blodgett method
- previous approaches
 - Pedersen et al.: plasma-polymerized hexane
low sensitivity, poor resolution (~ 150 nm)
 - Eric et al.: sterol resist named QSR-5
moderate resolution, noncommercial resist
 - Daniel et al.: water vapor, ice formation
special equipment, low sensitivity
 - similar issues with: CO_2 , AlF_3 , SiO_2



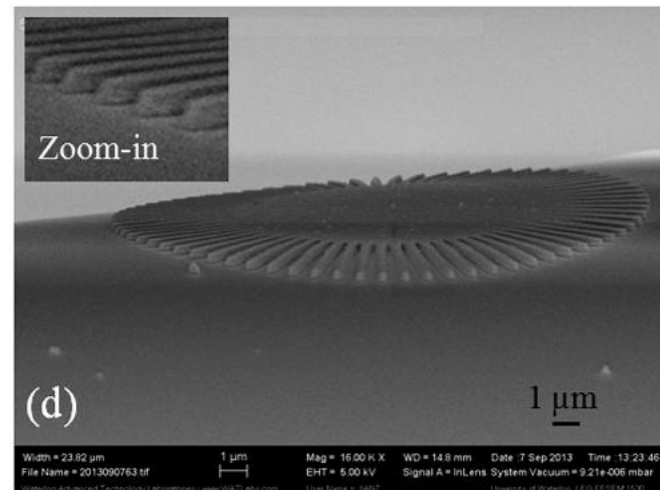
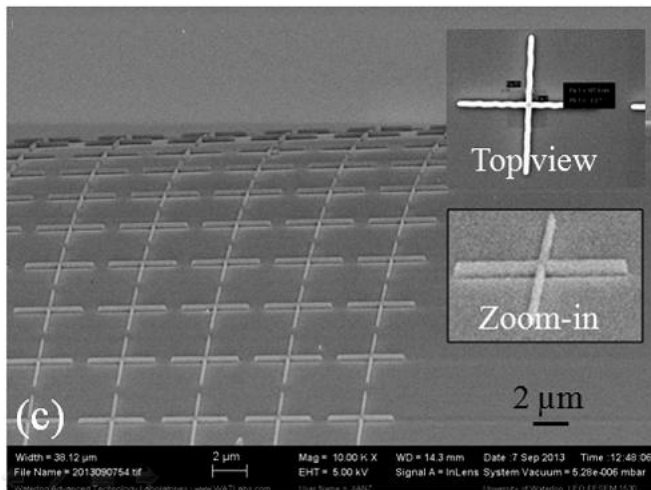
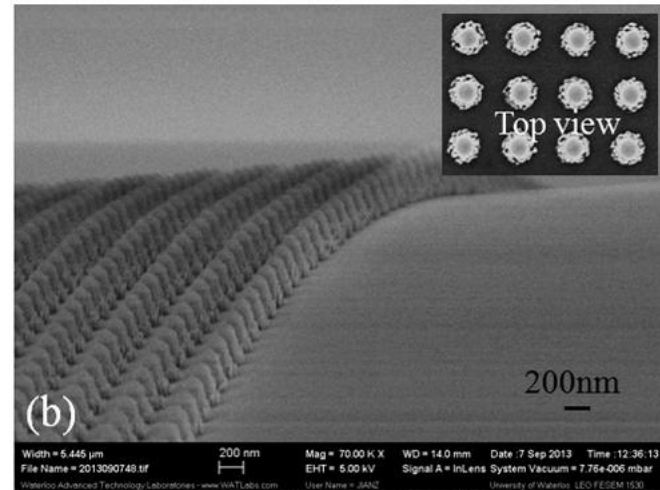
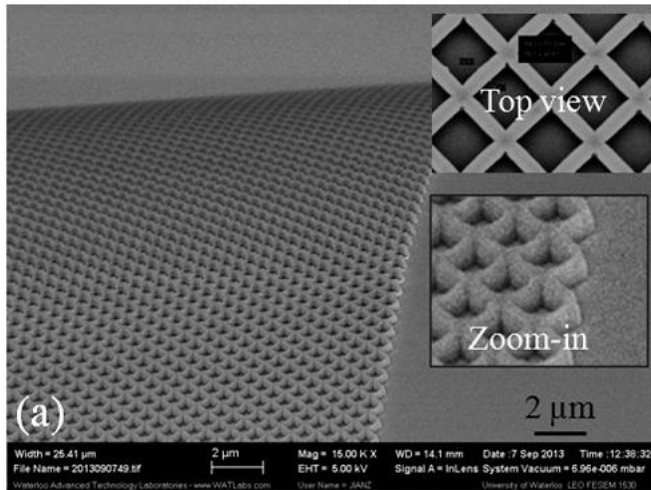
EBL with Evaporated Resist

- new approach
 - low molecular weight polystyrene (PS)
 - sensitivity lower than PMMA's
 $\sim 1 \text{ } \mu\text{eV}/\text{cm}^2$ @ 5keV
 - low dry etching rate
 - lack of edge bead effect (small wafers, e.g. single-crystal diamond)
 - precise control of film thickness
 - uniform coating (e.g. around dust particles)
 - negligible attack to the substrate material (e.g. a polymer susceptible to dissolution)
- resist parameters
 - roughness:
spin coated: 0.239
evaporated: 0.223
 - same IR spectrum \rightarrow no chemical modification during evaporation
 - sensitivity:
spin coated: $1920 \text{ } \mu\text{C}/\text{cm}^2$
evaporated: $4500 \text{ } \mu\text{C}/\text{cm}^2$
(lower molecular weight)



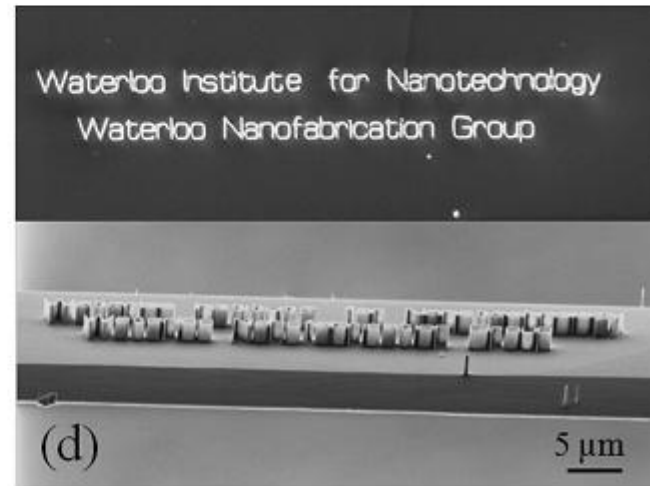
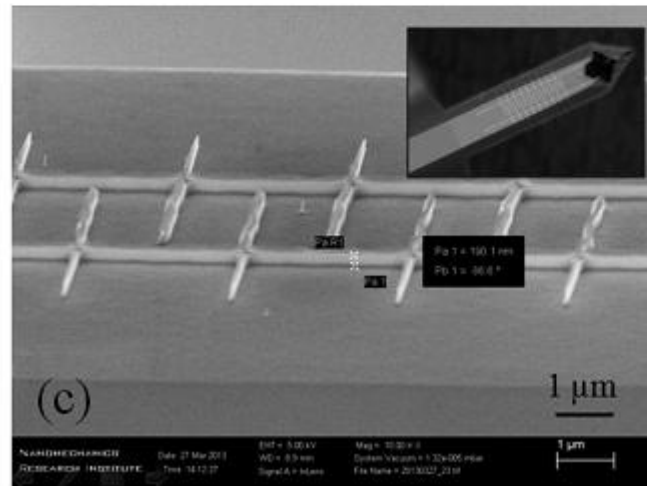
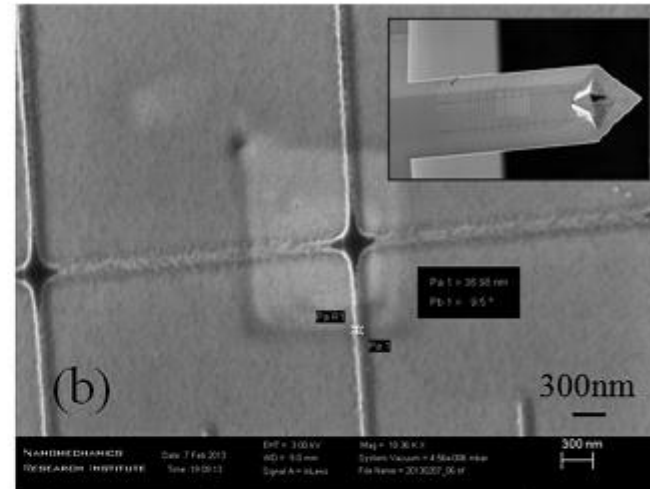
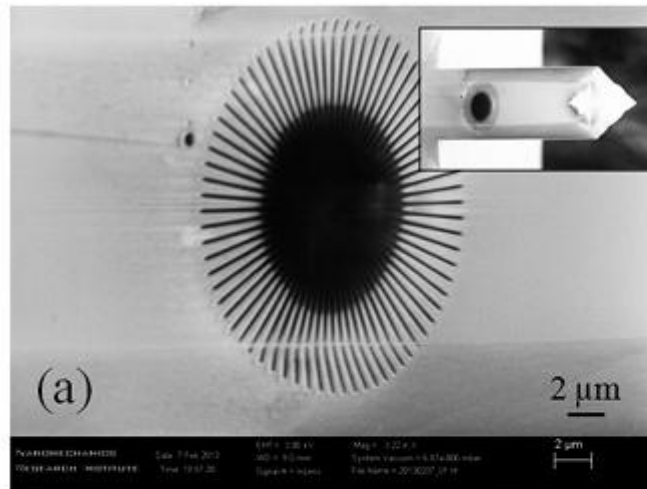
EBL with Evaporated Resist

- patterning an optical fiber



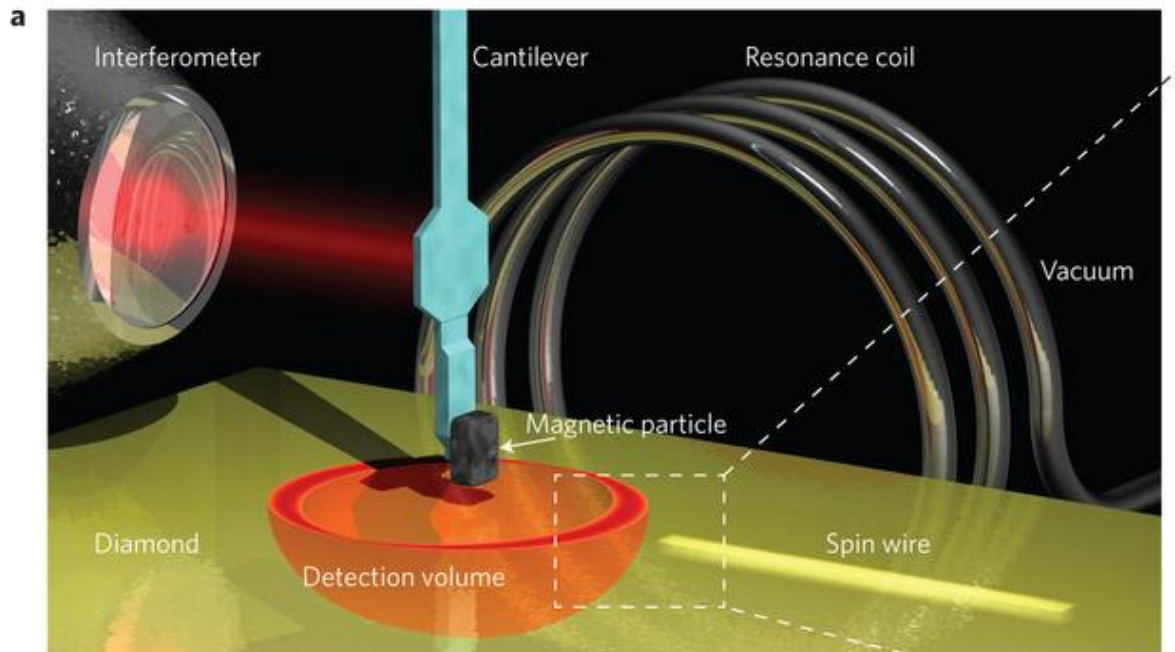
EBL with Evaporated Resist

- AFM cantilever



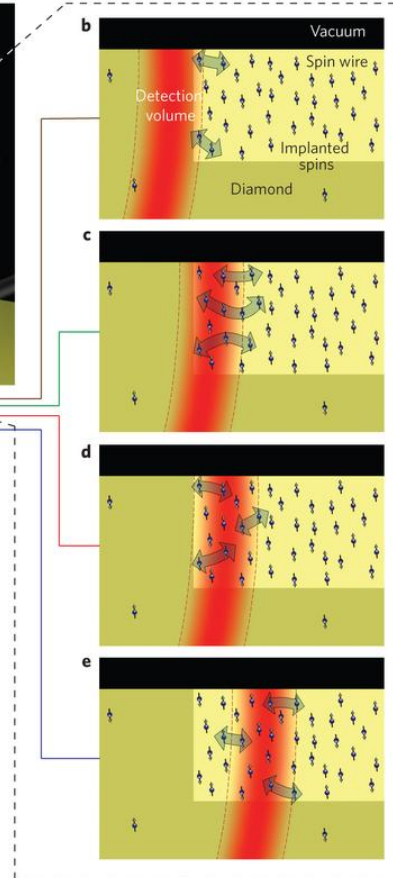
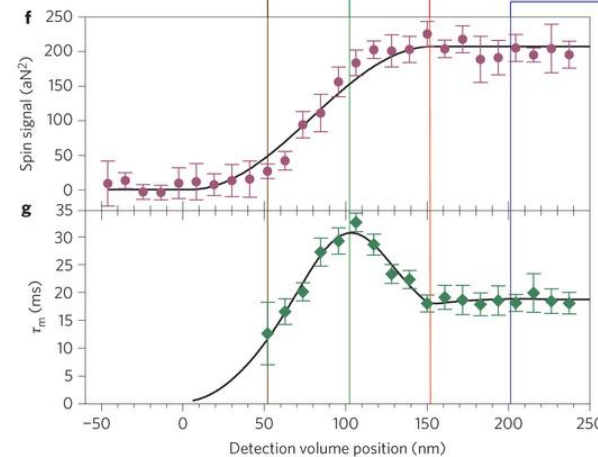
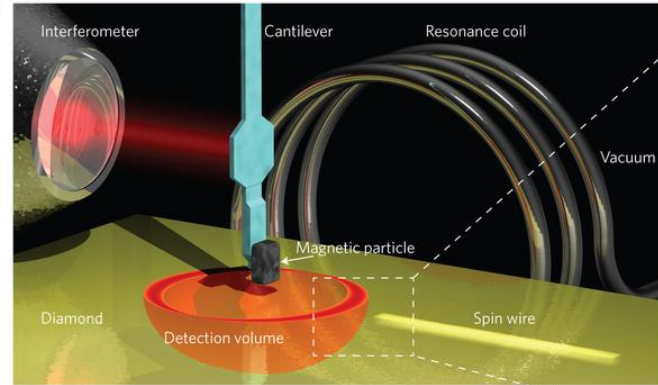
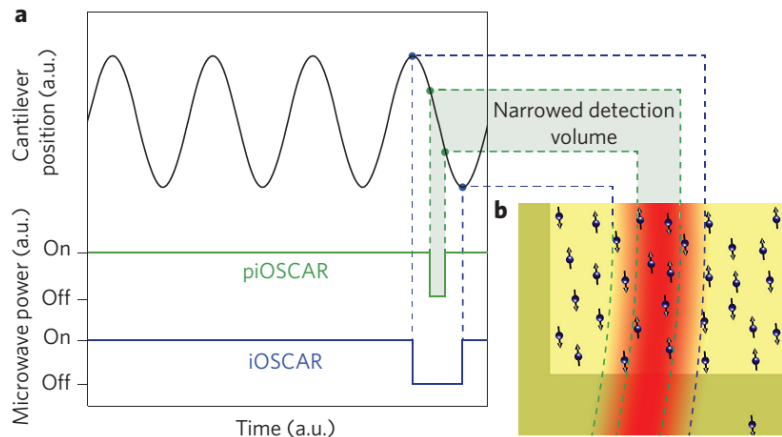
The effect of spin transport on spin lifetime in nanoscale systems

Jeremy Cardellino[†], Nicolas Scozzaro[†], Michael Herman, Andrew J. Berger, Chi Zhang, Kin Chung Fong, Ciriya Jayaprakash, Denis V. Pelekhov and P. Chris Hammel^{*}



The effect of spin transport on spin lifetime in nanoscale systems

- magnetic resonance force microscopy (MRFM)^a
- niobium coil: MW field, $f = 2.18$ GHz
- resonance field: $B = 77.8$ mT
(gyromagnetic ratio: 28 GHz/T)
- oscillating resonance slice
→ detection volume
- measurement of force on the cantilever
→ spin signal magnitude
from the magnitude of variance in the time record, directly related to the number of measured spins
→ force correlation time
describes the characteristic time for the net moment of the detected spins to decorrelate (spin transport, spin relaxation, etc.)



- force correlation time
- Monte Carlo simulation

flip-flop time $T_{ff} = 0.21$ ms
spin diffusion length $L = 700$ nm



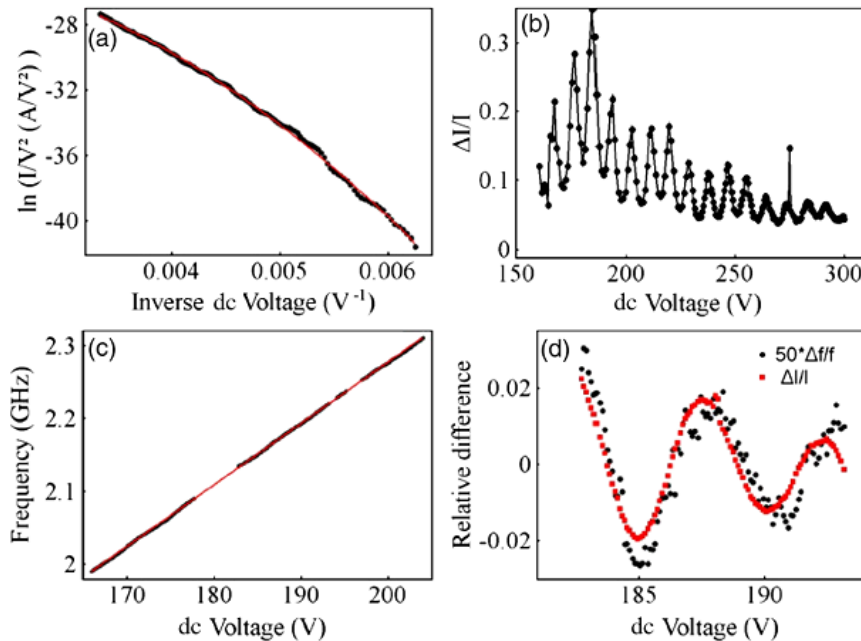
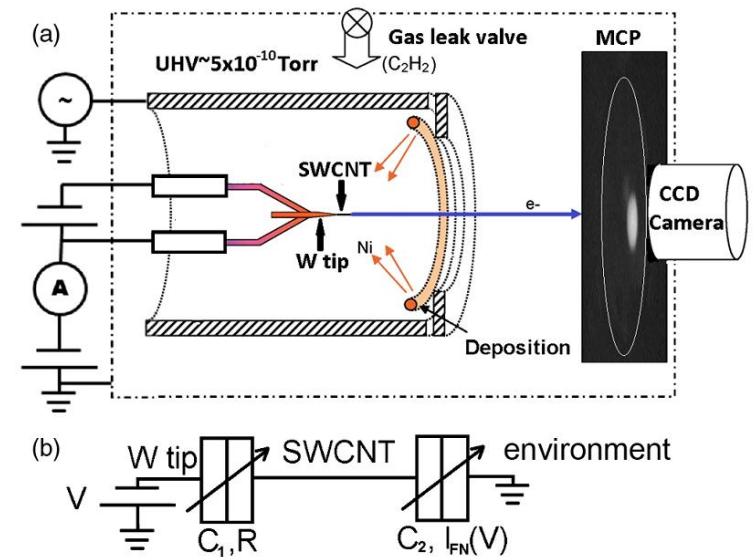
Ultrashort Single-Wall Carbon Nanotubes Reveal Field-Emission Coulomb Blockade and Highest Electron-Source Brightness

A. Pascale-Hamri, S. Perisanu,^{*} A. Derouet, C. Journet,[†] P. Vincent, A. Ayari, and S. T. Purcell
ILM, Université Claude Bernard Lyon 1 et CNRS, UMR 5586, F-69622 Villeurbanne, France

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Ultrashort Single-Wall Carbon Nanotubes Reveal Field-Emission Coulomb Blockade and Highest Electron-Source Brightness

- Coulomb blockade
two tunnel junctions + island
- field emission + Coulomb blockade
the most resistive junction is the vacuum barrier
- on-demand single electron source
- high brightness is needed for experiments
- for a RT application: $E_e > 25$ meV



- periodicity of 8.5 V in the $I(V)$ curve
- mechanical resonance frequency/capacitance
→ length
- current-induced shortening → period up to 80 V
- $C_1 \approx 100 C_2$
- I up to 1.8 μA